01 - Introduction to Radiation Effects in Microelectronics: What are radiation effects, where are radiation effects, terminology

ENGR-E 399/599

Microelectronics Radiation Effects and Reliability

Context

- **399: https://iu.instructure.com/courses/2251383**
- **599: https://iu.instructure.com/courses/2251419**

Topics in Intelligent Systems Engineering

Radiation Effects and Reliability of Microelectronics

Intelligent Systems Engineering, ENGR-E 399/599

Fall 2024

Full Term Course | INFO, CS, and ISE Majors Welcome

Lecture 3 Credit Hours

Course Start Date

This course begins the week of August 26, 2024

Artist depiction of solar flare imagery. Project ASSERT aims to quickly and reliably harden space-based microelectronics against damage caused by single-event effects, such as solar flares. Photo credit: Shutterstock via DARPA.

Course Description

This course introduces the space radiation environment and its effects on microelectronics. The basic mechanisms of cumulative and transient radiation effects in state-of-the-art semiconductor devices are discussed, with special focus on the challenges modeling, simulation, and measurement. Further, the implications of technology scaling are considered. Students will be exposed to industry standard tools and techniques for estimating the reliability of microelectronics in extreme space environments.

Course Pre-Requisites: None

Course Co-Requisites: None

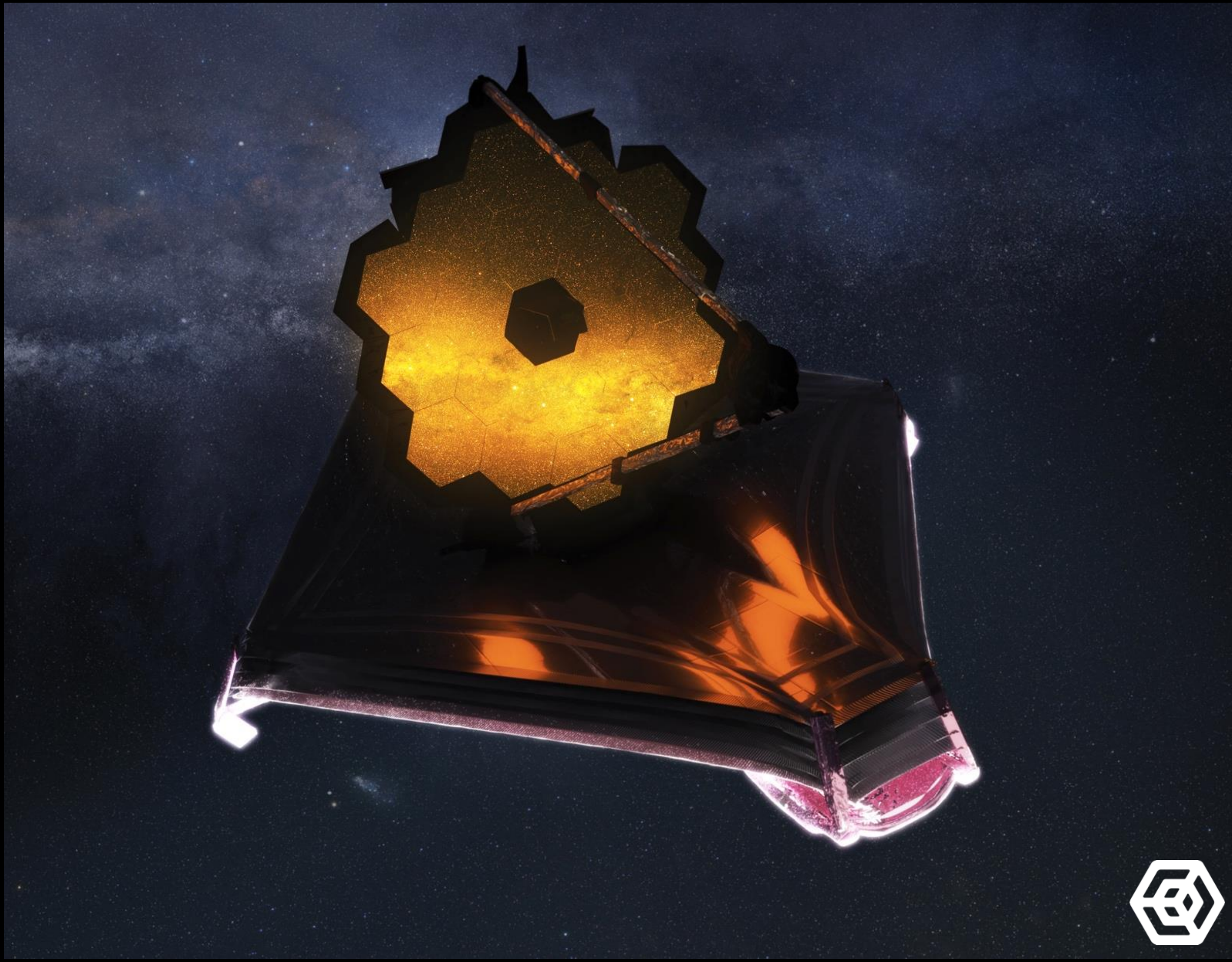
Quick Facts about the Hubble Space Telescope:

- Approximate size: 43 ft x 14 ft
- Weight: 24,000 lbs (11,110 kg)
- Cost at launch: $1.5 billion (1990)
- Can hold steady at about 7/1000th of an arcsecond (~ the width of a human hair seen at 1 mile)

The Hubble Space Telescope, 2003
http://hubblesite.org/

Fun Facts about the Webb Telescope:

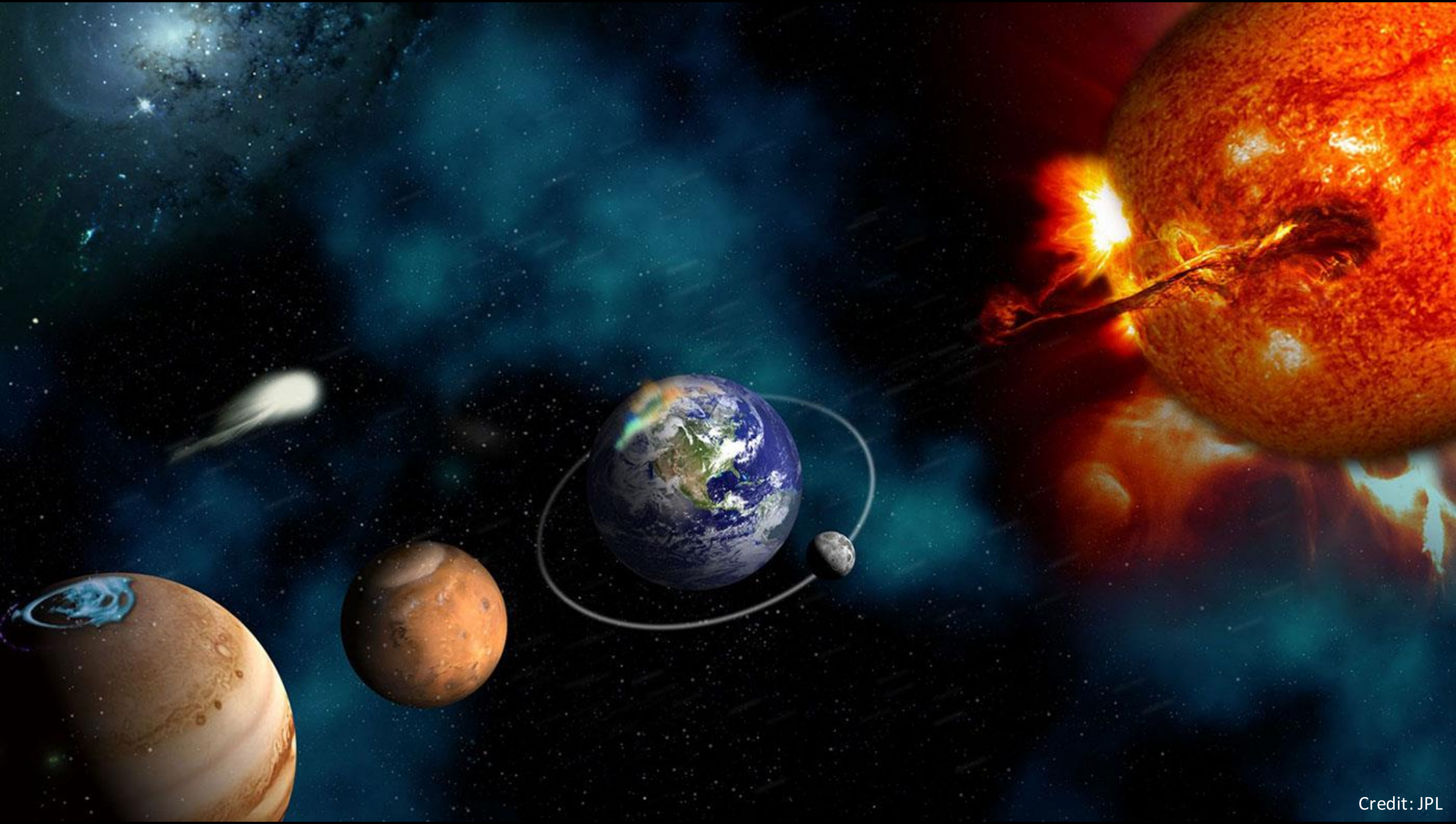
- Approximate size: 66 ft x 46 ft
- Cost at launch: $10 billion (2021)
- Can detect the heat signature of a bumblebee at a distance from the Earth to the Moon



Webb Space Telescope, 2022
https://webb.nasa.gov/

Falcon 9 barge landing after delivery of 10 Iridium NEXT satellites into orbit, Jan. 14, 2017.

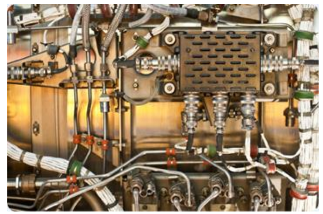
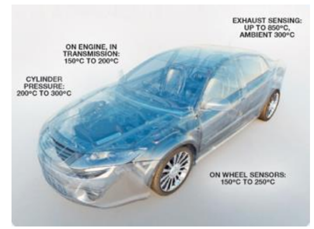
Credit: SpaceX

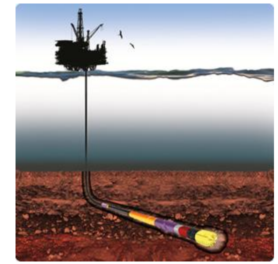


Credit: JPL

Context

- **Many applications require electronic devices to operate in extreme environments that can impact operation and reliability**
  - Vibration/shock
  - Temperature
  - Pressure
  - Radiation

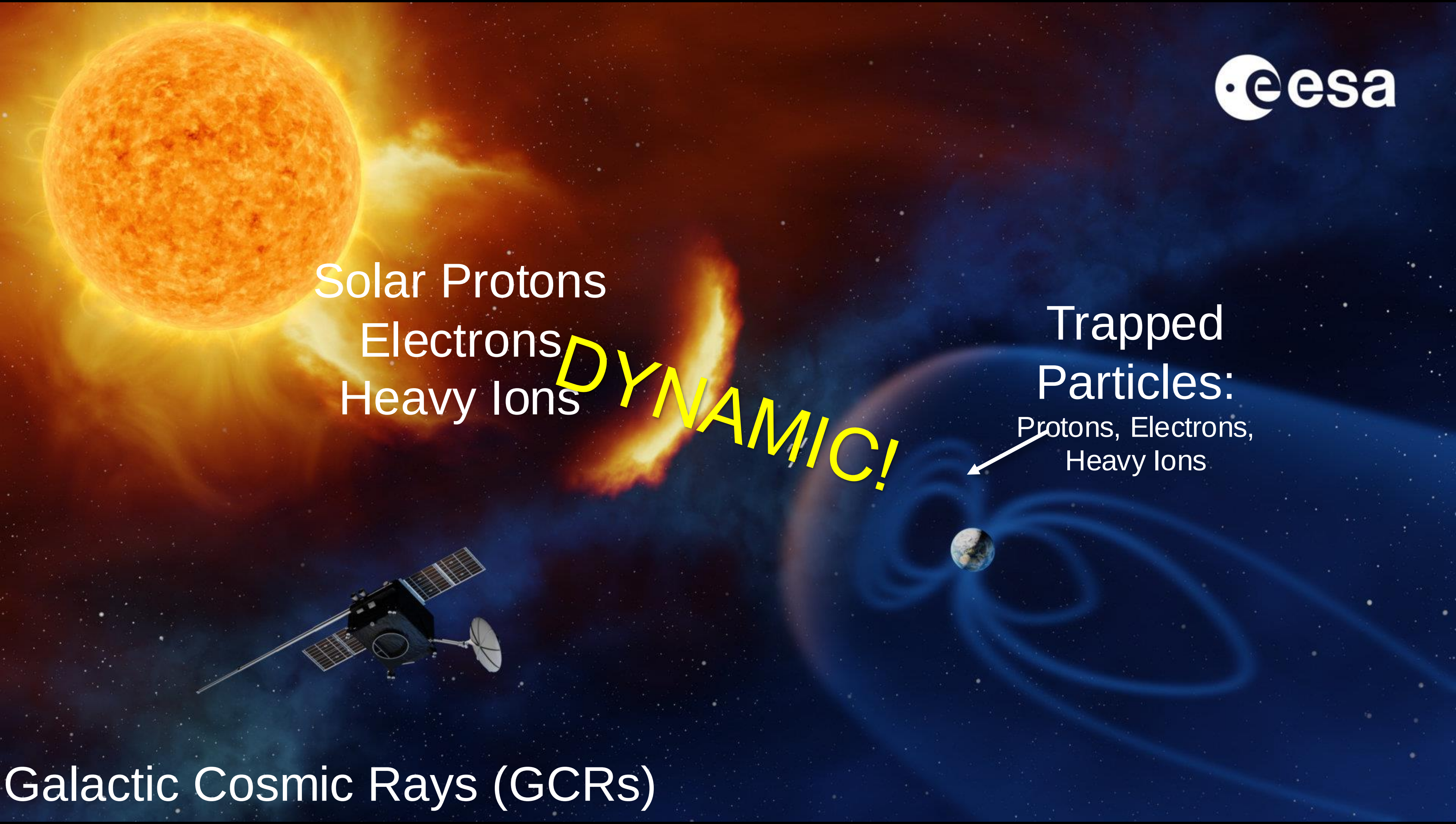


- **Natural and mand-made radiation environments**
  - Space
  - Nuclear Power
  - Weapons
  - Medical
  - Terrestrial







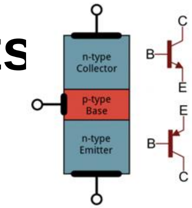

Solar Protons
Electrons
Heavy Ions
DYNAMIC!
Trapped
Particles:
Protons, Electrons,
Heavy Ions
Galactic Cosmic Rays (GCRs)

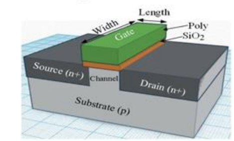
General Characteristics: Radiation Effects in Electronics

- Radiation (photons or particles) transfers energy to materials used in electronics devices
- Mechanisms and manifestations of the energy transfer depend on the material (esp. semiconductor or insulator), characteristics of the radiation, and device type
- Processes can be ionizing (linear energy transfer, LET) or non-ionizing (non-ionizing energy loss, NIEL)
- Interactions may be localized or systematic depending on the radiation type
- Effects may be transient or persistent, and may be recoverable or destructive

Radiation Effects in Electronics - Impact

- Transistors are the basic building blocks of circuits
  - Act like a switch in digital circuits
  - Act like a rheostat in analog circuits

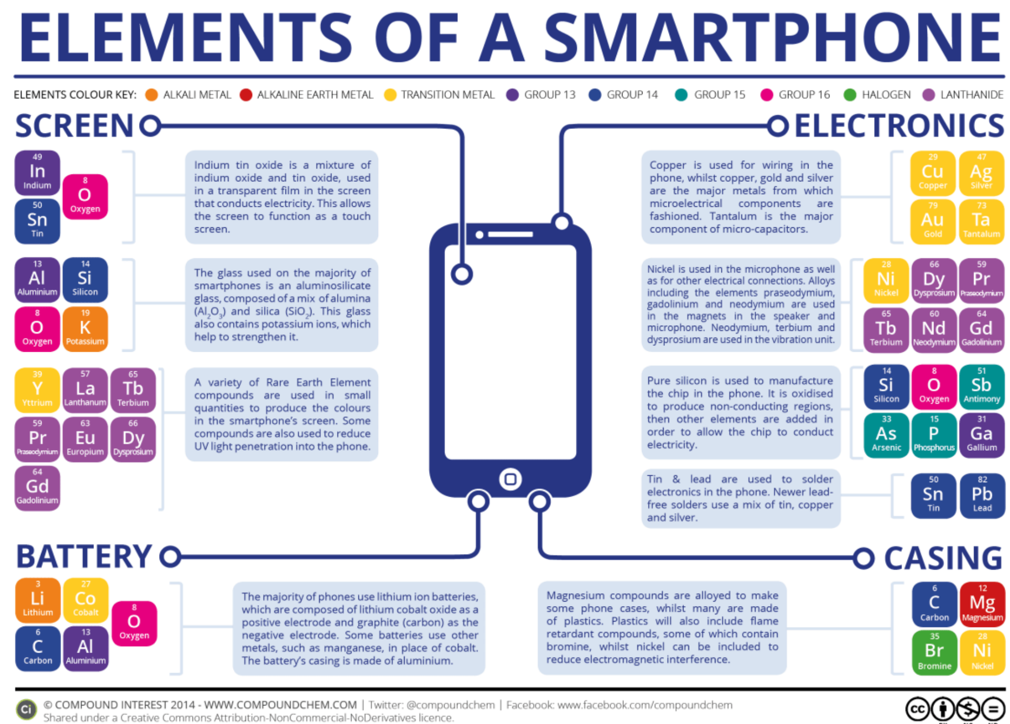


- Radiation can cause one or more of these “switches” to turn on for short times (~ pico to micro seconds), cause the switches to “leak” electricity (increased leakage current), or change the turn-on voltages

- This can result in digital errors (state changes), device burnout, increased standby power consumptions, slower operation, loss of proper functionality

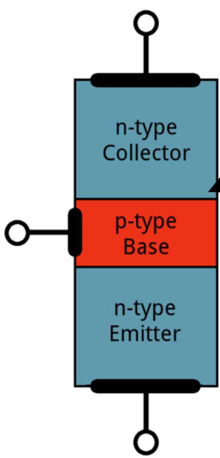
Electronic Devices – Material Types

- **Electronic circuits are generally composed of three types of materials:**
  - **Semiconductors**
  - **Insulators**
  - **Conductors (metals)**

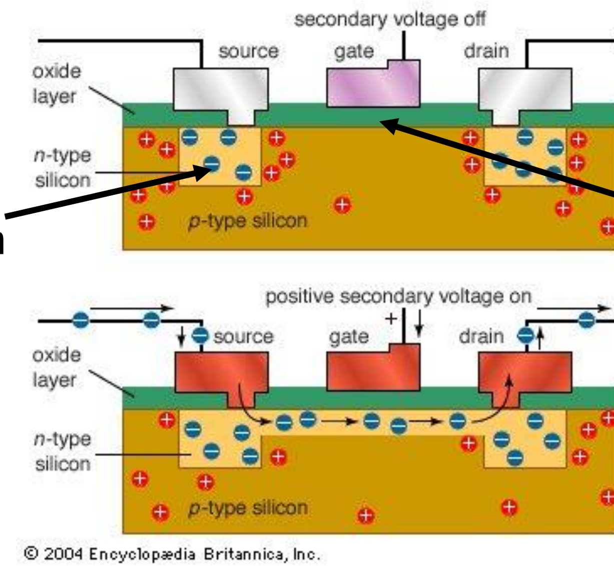


Transistor Basics

- Transistors are generally comprised of semiconductor p-n junctions and capacitors, contacted by metal conductors, all built on top of a substrate for mechanical support
- The most common types are bipolar junction and metal-oxide-semiconductor field-effect transistors (BJTs, MOSFETs) although there are many others



Both BJTs and MOSFETs contain p-n junctions



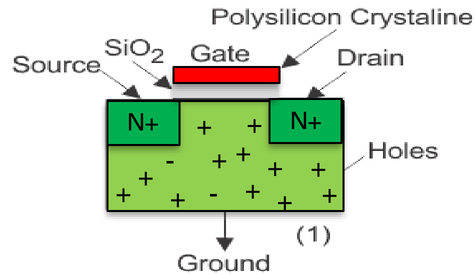
MOSFETs use a capacitor to “gate” the conduction via a field effect

https://cdn.sparkfun.com/assets/learn_tutorials/1/9/3/transistor-construction.png

https://www.britannica.com/technology/transistor

Background: The Transistor

- Bipolar Junction Transistor (BJT):
  - Invented in 1947 (Bell Labs)
  - Relies on conduction by holes **and** electrons
  - Most common transistor in the 60s and 70s
- Field Effect Transistor (FET):
  - Conceptualized in the 20s and thoroughly explained by Bell Labs in 1948
  - Relies on conduction by **either** holes **or** electrons
  - Metal Oxide Semiconductor FET (MOSFET) invented in late 1950s (currently the most common transistor)



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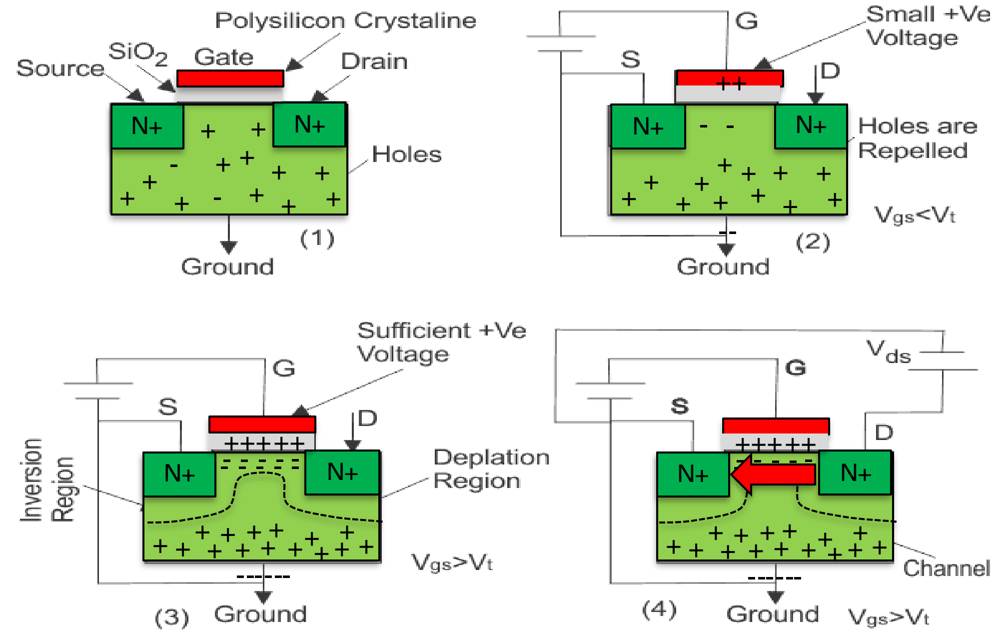


STOP: Take a moment and create an account on nanoHUB.org

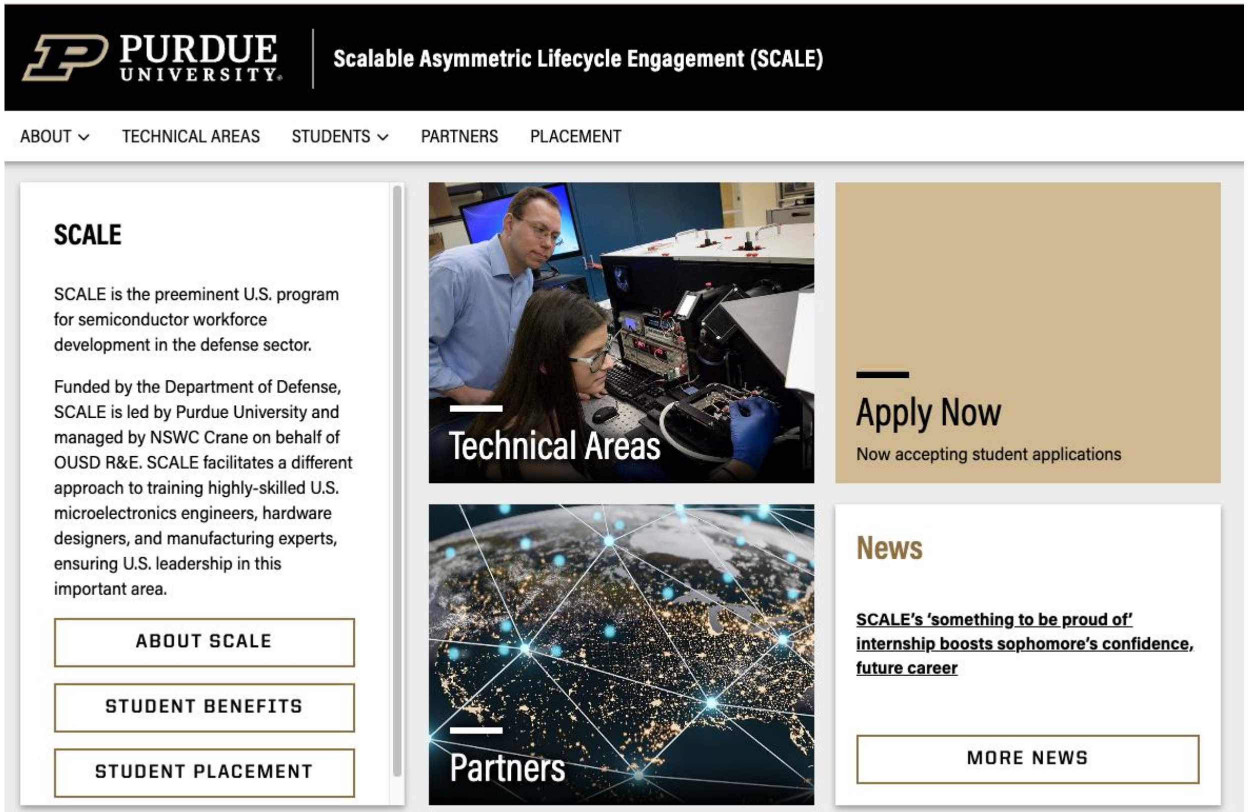
Some useful tools and visuals:

https://www.circuitsgallery.com/mosfet-working/

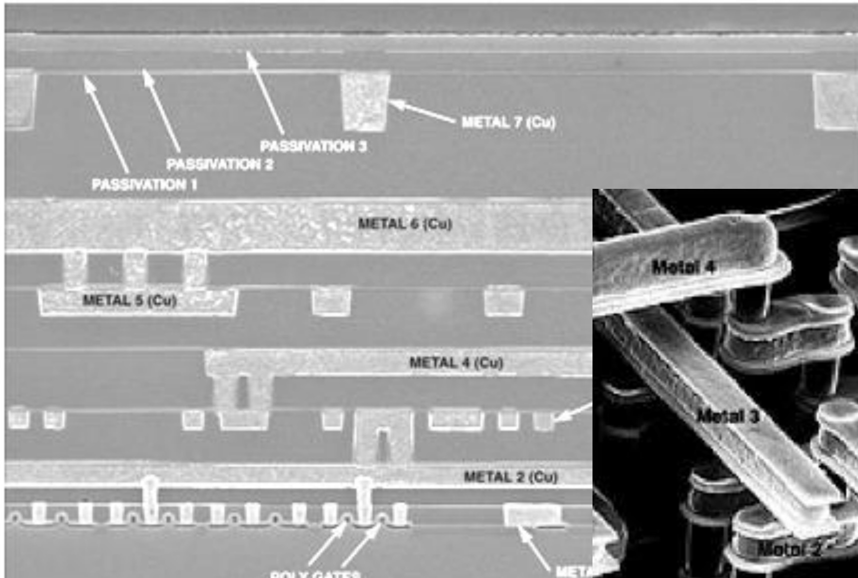
nanoHUB (MOSfet, MOSFET Simulation, ABACUS)

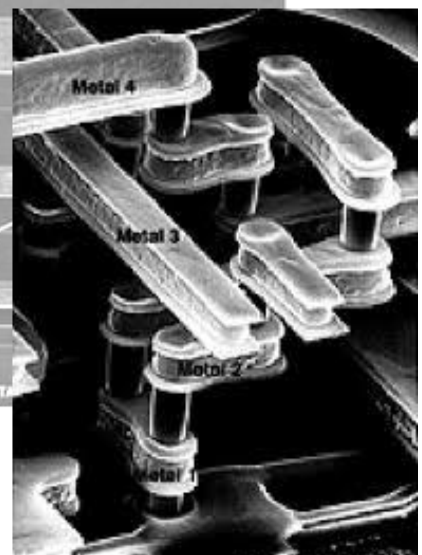
SCALE

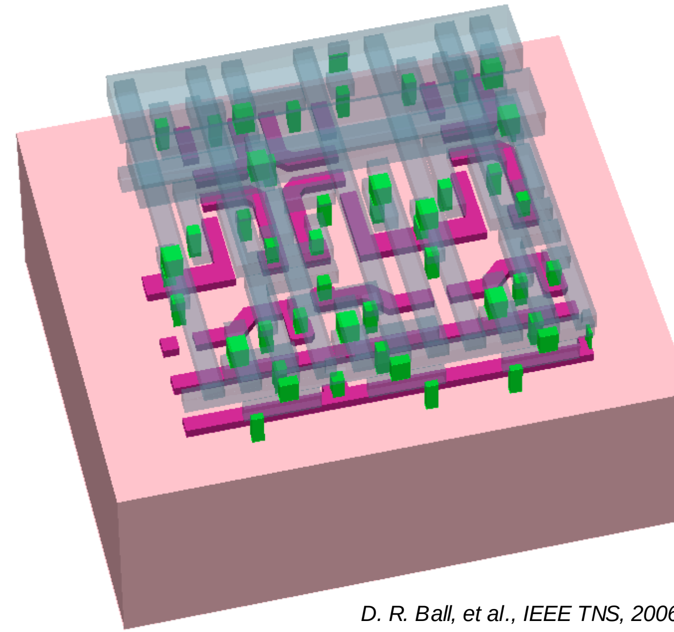
https://research.purdue.edu/scale/



Modern Integrated Circuits (ICs)?

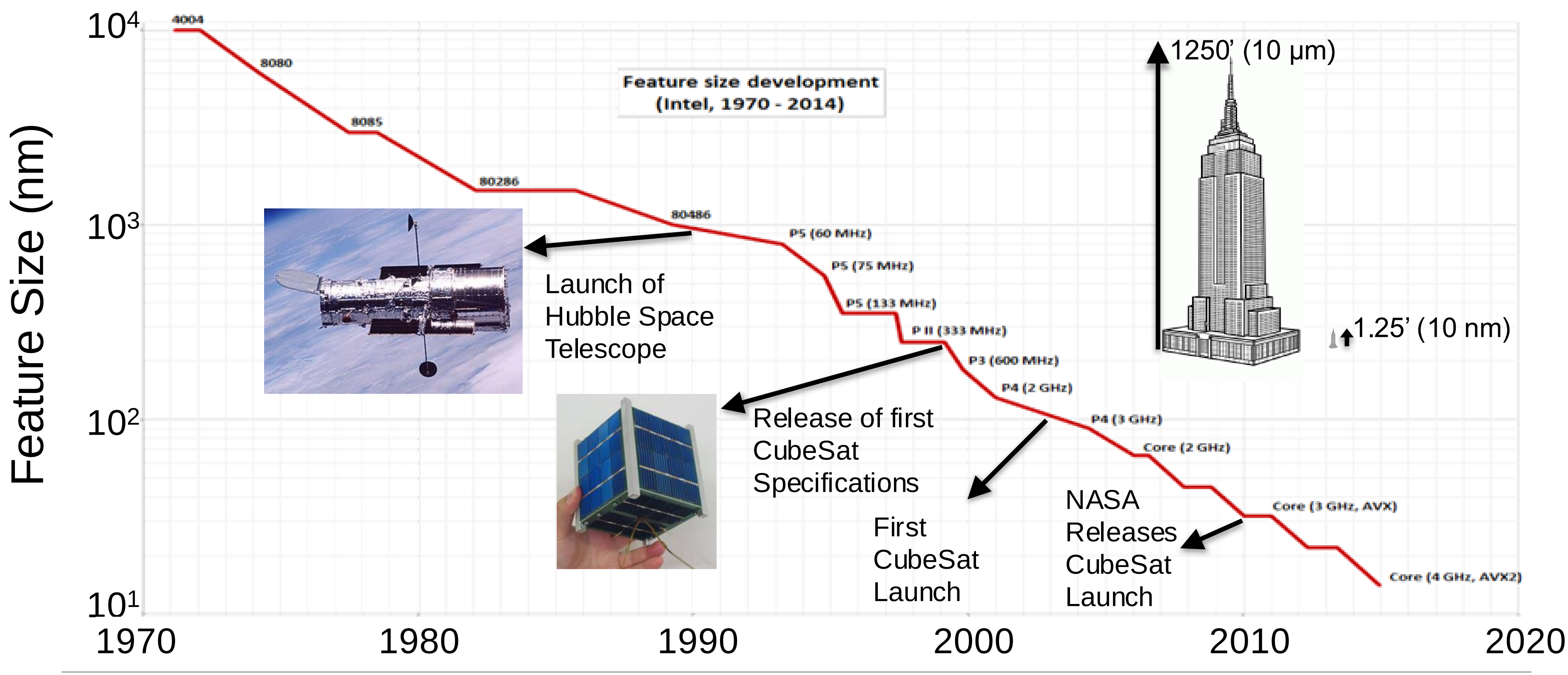




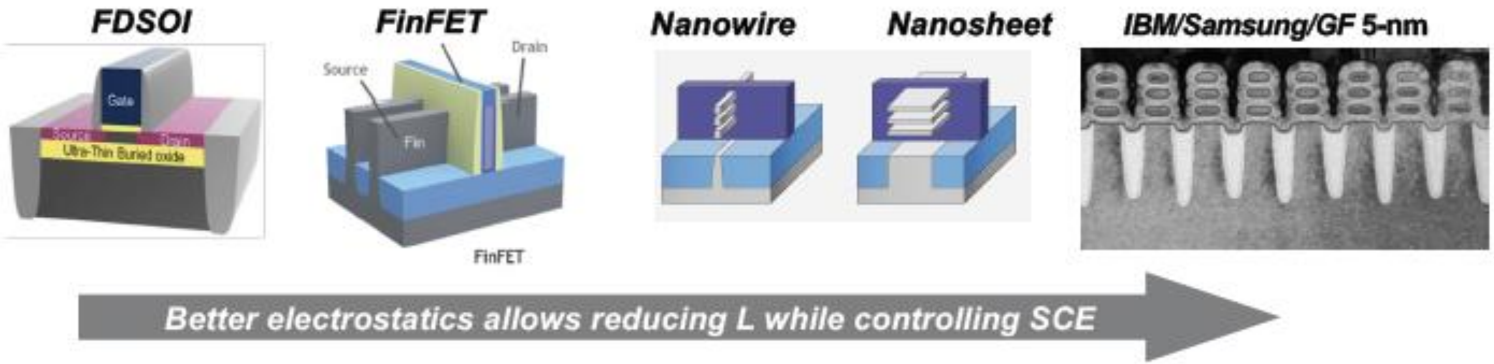


D. R. Ball, et al., IEEE TNS, 2006

Feature Size Development (Intel)

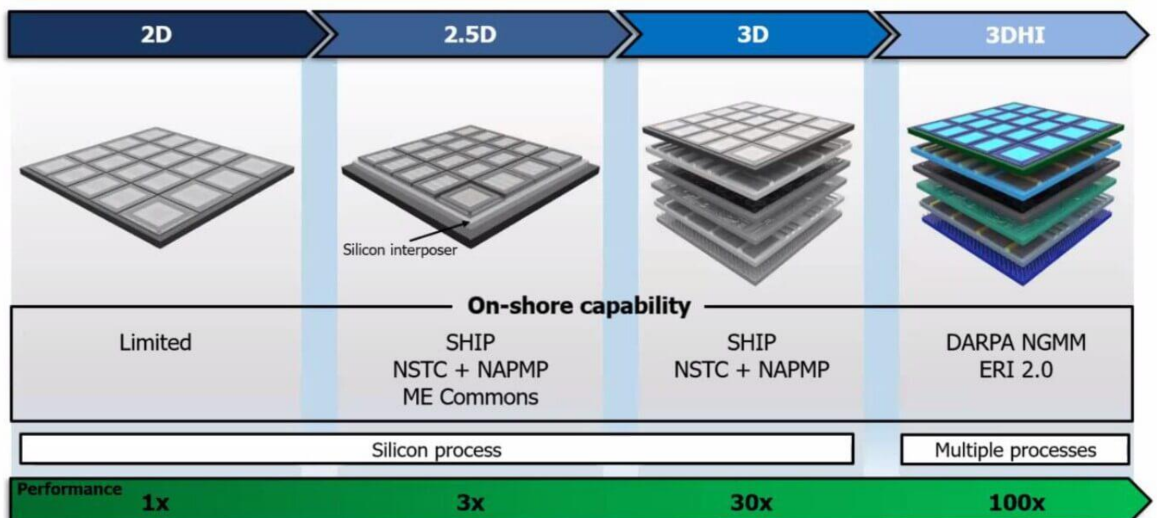


Modern Integrated Circuits



Esqueda, JPL Workshop, 2019

**SCE: Short-Channel Effects*



Manufacturing capabilities are stacking up. (Source: DARPA)

Manufacturing Facilities are Diminishing

Number of Semiconductor Manufacturers with a Cutting Edge Logic Fab

SilTerra										
X-FAB										
Dongbu HiTek										
ADI	ADI									
Atmel	Atmel									
Rohm	Rohm									
Sanyo	Sanyo									
Mitsubishi	Mitsubishi									
ON	ON									
Hitachi	Hitachi									
Cypress	Cypress	Cypress								
SkyWater	SkyWater	SkyWater								
Sony	Sony	Sony								
Infineon	Infineon	Infineon								
Sharp	Sharp	Sharp								
Freescale	Freescale	Freescale								
Renesas (NEC)	Renesas	Renesas	Renesas	Renesas						
Toshiba	Toshiba	Toshiba	Toshiba	Toshiba						
Fujitsu	Fujitsu	Fujitsu	Fujitsu	Fujitsu						
TI	TI	TI	TI	TI						
Panasonic	Panasonic	Panasonic	Panasonic	Panasonic	Panasonic					
STMicroelectronics	STM	STM	STM	STM	STM					
HLMC	HLMC		HLMC	HLMC	HLMC					
IBM	IBM	IBM	IBM	IBM	IBM	IBM				
UMC	UMC	UMC	UMC	UMC	UMC		UMC			
SMIC	SMIC	SMIC	SMIC	SMIC	SMIC		SMIC			
AMD	AMD	AMD	GlobalFoundries	GF	GF	GF	GF			
Samsung	Samsung	Samsung	Samsung	Samsung	Samsung	Samsung	Samsung	Samsung	Samsung	Samsung
TSMC	TSMC	TSMC	TSMC	TSMC	TSMC	TSMC	TSMC	TSMC	TSMC	TSMC
Intel	Intel	Intel	Intel	Intel	Intel	Intel	Intel	Intel	Intel	Intel
180 nm	130 nm	90 nm	65 nm	45 nm/40 nm	32 nm/28 nm	22 nm/20 nm	16 nm/14 nm	10 nm	7 nm	5 nm

https://en.wikichip.org/wiki/technology_node

Technology is Evolving Rapidly, So Must Education and Workforce

By 2030 …

300,000

Shortage of engineers

90,000

Shortage of skilled workers

Source: https://www.mckinsey.com/industries/semiconductors/our-insights/how-semiconductor-makers-can-turn-a-talent-challenge-into-a-competitive-advantage

Process *vs* **Ecosystem**

Process

- Multiple participants with well-defined roles
- Designed for an end customer
- Participants may have different interests but work towards shared goal
- Repeatable, predictable, and measurable outputs
- Regular paths to uniform outputs

Ecosystem

- Multiple participants with **diverse roles**
- **Naturally evolves** to meet diverse needs of all participants
- Participants may have different interests and sometimes even competing interests
- Evolving outcomes and **adaptation to changing circumstances**
- Diverse paths to variable outcomes, even for similar participants

Source: deloitte.com/insights

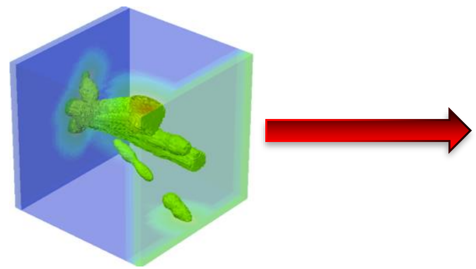
Radiation Effect Types

- **Transient-radiation effect - generally refers to the impact of charge generation and resulting transient currents in the active semiconductor portion of electronic devices**
  - Single-event effects (SEE)
  - Transient-dose effects (prompt dose, gamma-dot)
- **Total-ionizing dose (TID) - generally refers to the impact of charge generation, and resulting distributions of excess charge within the insulating portions of electronic devices**
- **Displacement damage dose – deposited energy does physical damage, specifically displacement damage, in the insulators and/or active regions**
- **Electro Magnetic Pulse (EMP) - EM energy may couple into systems via antenna effect**

Single-Event Effects (SEE)

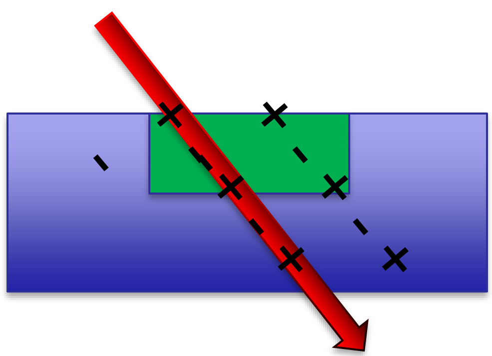
The primary terrestrial and a significant space radiation effect

- **Directly change the state of one or more memory cells or latches**
  - Single-event upset (SEU) or soft error
  - Frequency referred to as Soft-Error Rate (SER) or Failure in Time (FIT) rate
- **Single events induce transients (SETs) that can propagate to a latch and become and error**
- **SETs can disrupt analog and RF operation**
- **Single events can induce high current start (latchup = SEL) and resulting in burnout (single-event burnout, SEB)**
- **Single events can cause hard errors such as gate rupture (generally not concern in very thin insulators in terrestrial environments)**

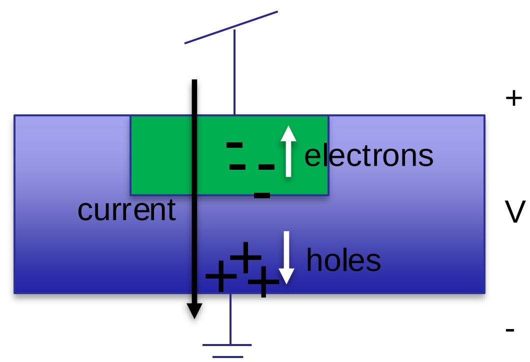


Single-Event Effects in Microelectronics

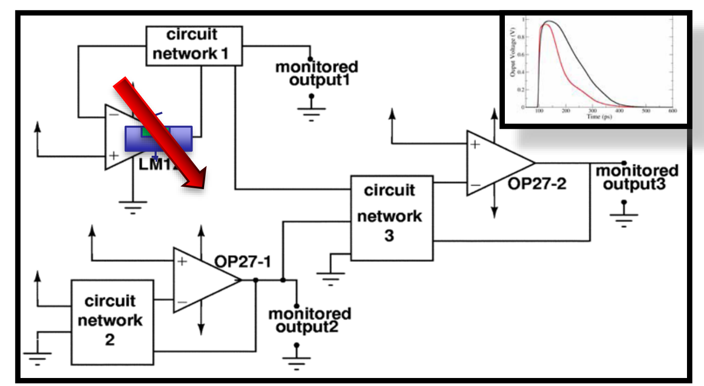
- Caused by the interaction of a single energetic particle
- SEE are determined by:
  - Charge generation
  - Charge collection
  - Circuit response



Charge generation (fs)

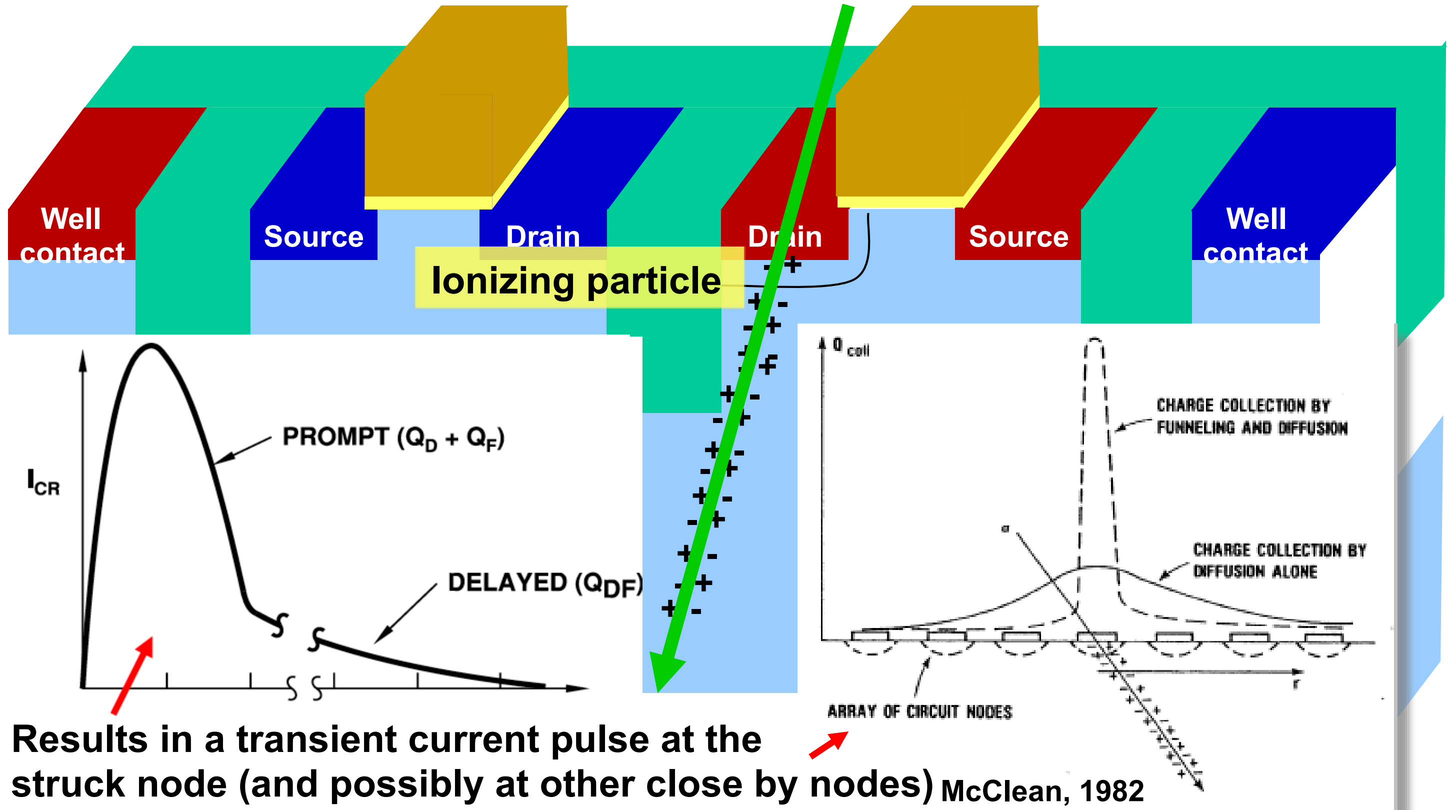


Charge collection (ps-ns)



Circuit Response (ps – ms)

Single-Event Charge Collection



Results in a transient current pulse at the struck node (and possibly at other close by nodes)

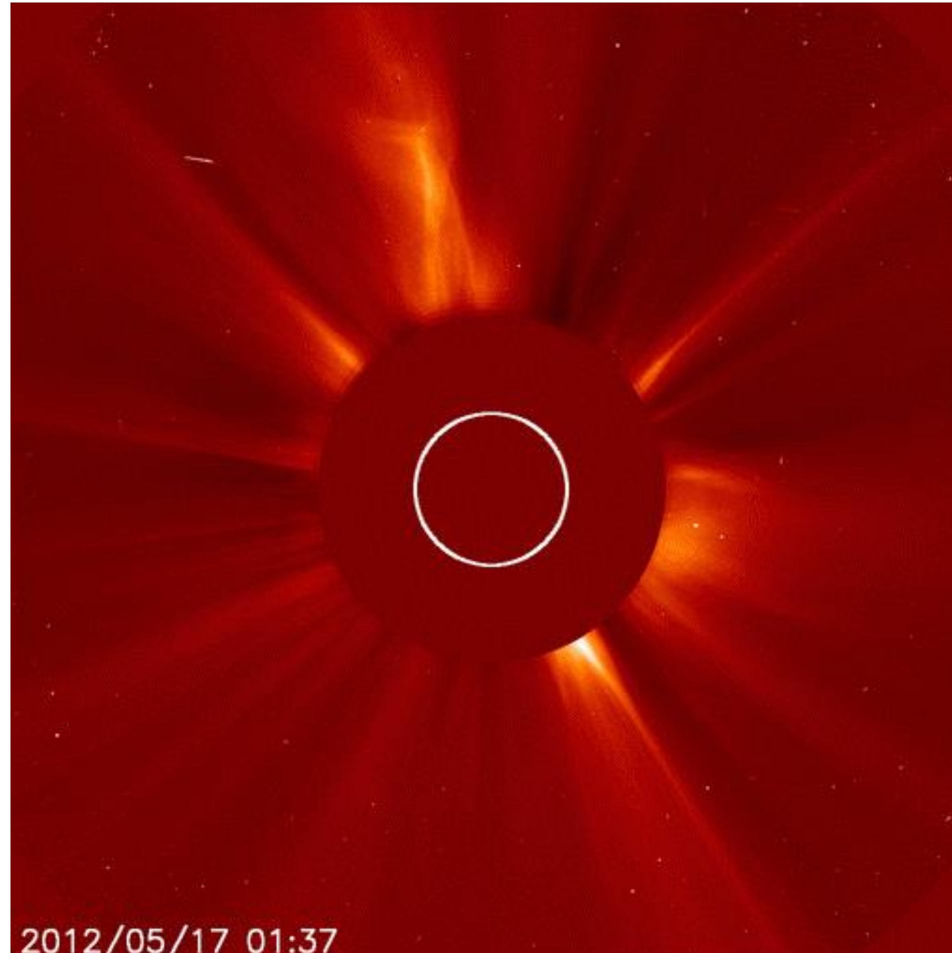
Multi-node effects are major consideration in < 90 nm bulk CMOS

Coronal Mass Ejection

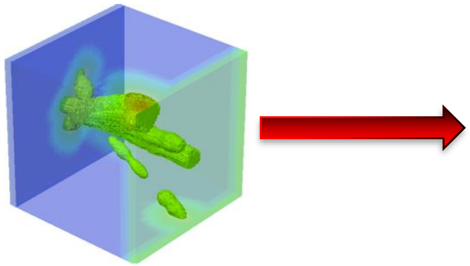
NASA on May 16-17th, 2012:

A coronal mass ejection (CME) was associated with a M-class solar flare occurring on May 16th. The burst traveled over 930 mps and impacted a variety of spacecraft. The flare also resulted in a moderate radio blackout.

http://www.nasa.gov/mission_pages/sunearth/news/News050912-Mflares.html



http://www.spaceweather.com/archive.php?view=1&day=18&month=05&year=2012



Single-Event Effects in Microelectronics

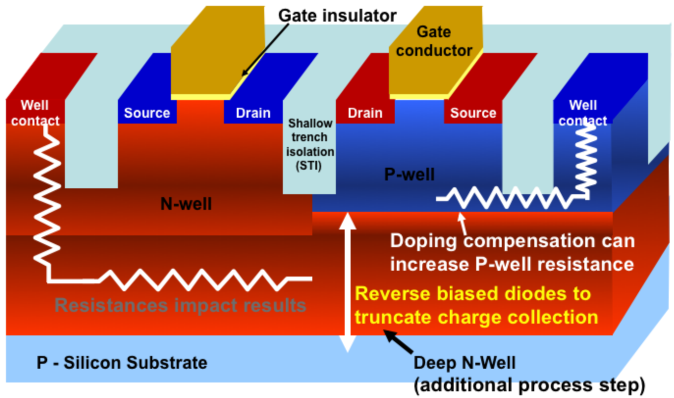
- Caused by the interaction of a single energetic particle
- SEE are determined by:
  - Charge generation
  - Charge collection
  - Circuit response

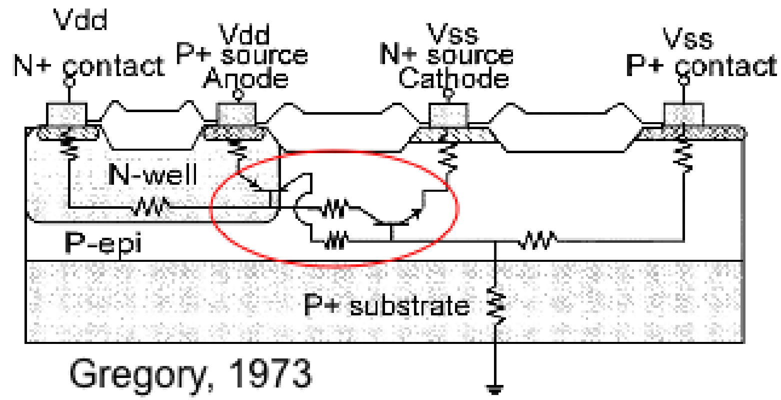
- Types:

  Non-destructive:
  - **Single-event upsets (soft errors)**
  - **Single-event transients**
  - Single-event functional interrupt
  - Multiple-bit upsets

  Destructive:
  - **Single-event latchup**
  - Single-event burnout
  - Single-event gate rupture
  - Single-event snap-back

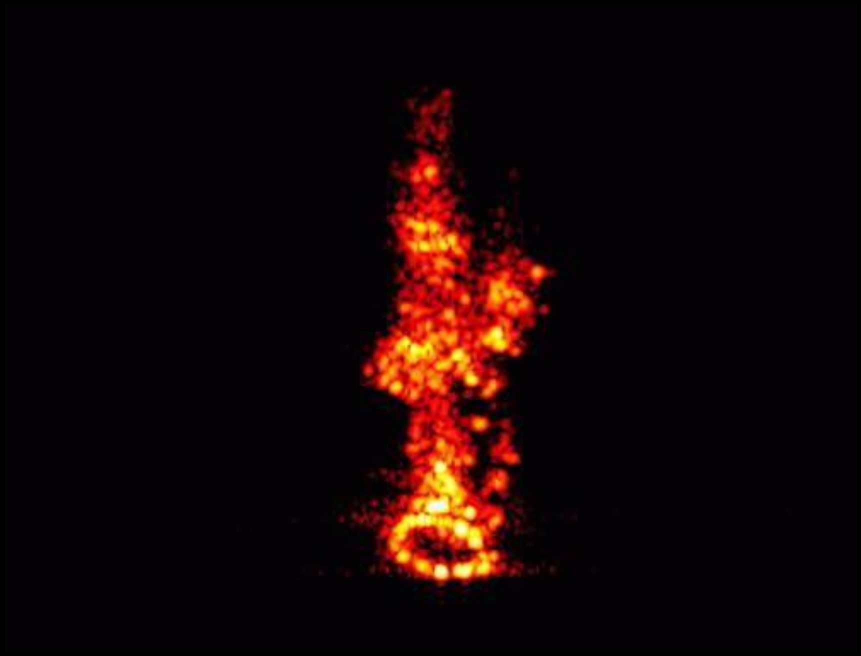
Single-Event Latchup (SEL)





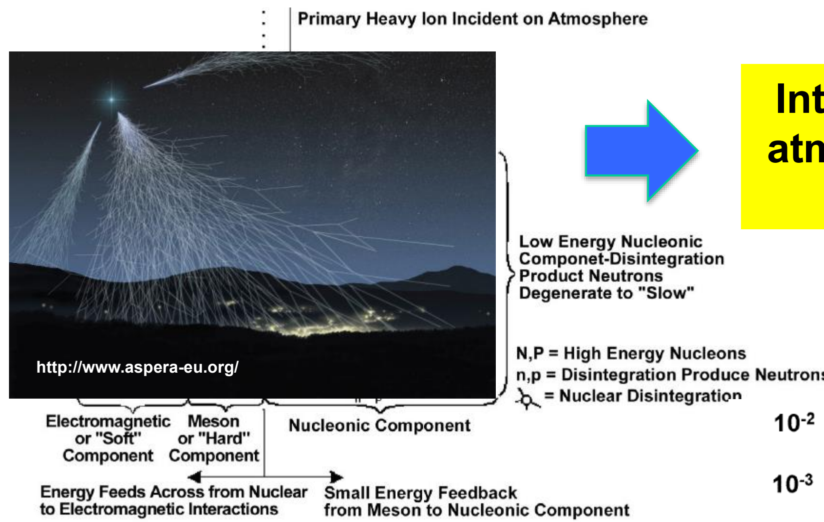
Single event can trigger sub-surface bipolar structures in positive feedback loop in bulk CMOS = Single Event Latchup

Phobos-Grunt Failure



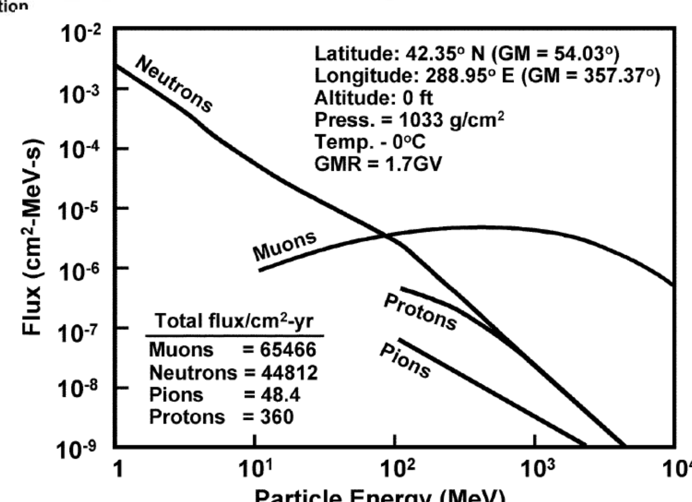
Phobos-Grunt re-entry after mission failure
SEL?

SEE – Terrestrial Radiation



Interaction of radiation with the atmosphere results in terrestrial radiation environment

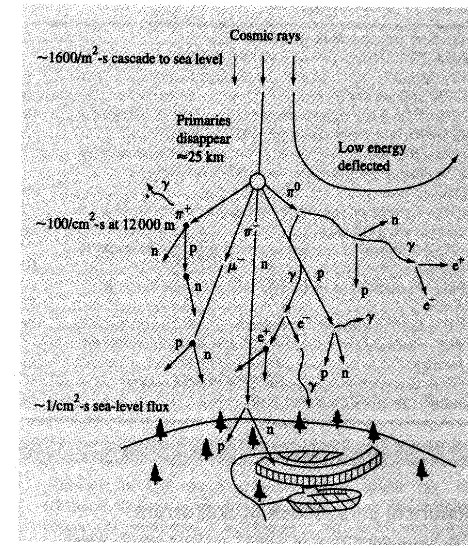
Interact with materials used in microelectronic leading to damage or ionization; processes may include secondary reaction products

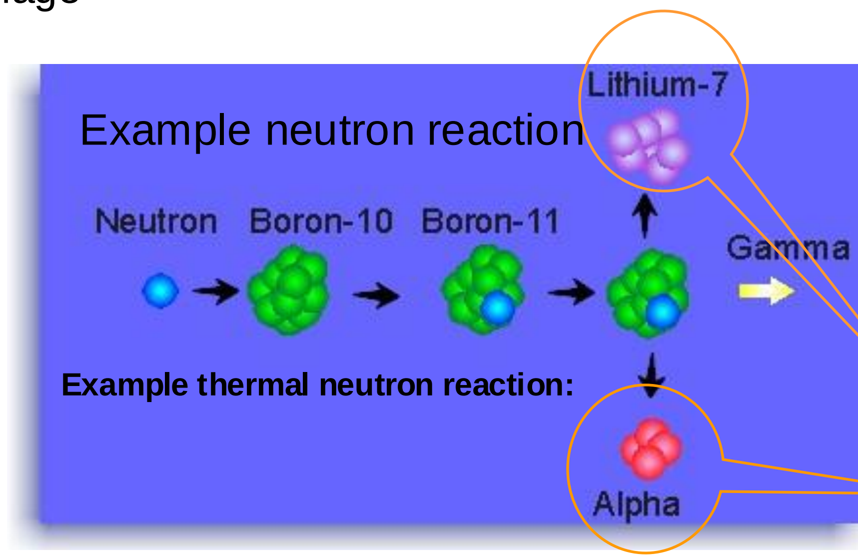


J. L. Barth IEEE Trans. Nucl. Sci., 50, 3, June 2003, pp. 469 (Ziegler/IBM).

SEE – Terrestrial Neutrons

1. Neutrons are created by cosmic ion interactions with oxygen and nitrogen in the upper atmosphere
2. Interact with material (**esp. ^{10}B**) in the electronic devices
3. Reaction products (including protons, alphas, ions) deposit excess charge or displacement damage





Energy; Range;
Time of Flight; Total Charge

0.8 MeV; 2.4μm; 1.5ps; 36fC

1.5 MeV; 5.2μm; 2.4ps; 67fC

SEE - Alpha Particles (He++) and Packaging

- **Packaging contaminants leading to SEE problems in the early 80's: U-238, Y-235, Th232 , Energies: 4 - 9 MeV**
- **Ionizing alpha particles also come from packaging materials**
- **Pb solder is the biggest contributor**
- **Flip chip and 3D stacking increase Pb proximity to devices**
- **Low alpha Pb costs ~ 5-400X more per pound**

Sources
Solders
Alumina substrates
BEOL metallizations
Fillers in plastics, encapsulants, underfills, mold compounds and solder masks
Flux
Lead frame alloys
Materials (Au, Cu, Ag etc) used for wire bonding and lid plating
Particulates from PBGA trimming / handling operations

Material	Alpha radiation flux (a/khr cm^2)
Processed wafers	0.9
Cu metal (thick)	1.9
Al metal (thick)	1.4
Mold compound	24 to < 2
Underfill	2 to 0.9
Pb solders	7200 to < 2
LC II Pb (HEM)	50 to 3
LC I Pb (HEM)	1000 to 130
Alloy 42 (Hitachi)	8
Au-plated alloy 42 (HEM)	4
Sn (HEM)	>1000 to <1
AlSiC (Lanxide)	215
LC6 Al (HEM)	8

S. Kumar et al., Rev. Adv. Mater. Sci 34 (2013) 185-202

Space Radiation Environment

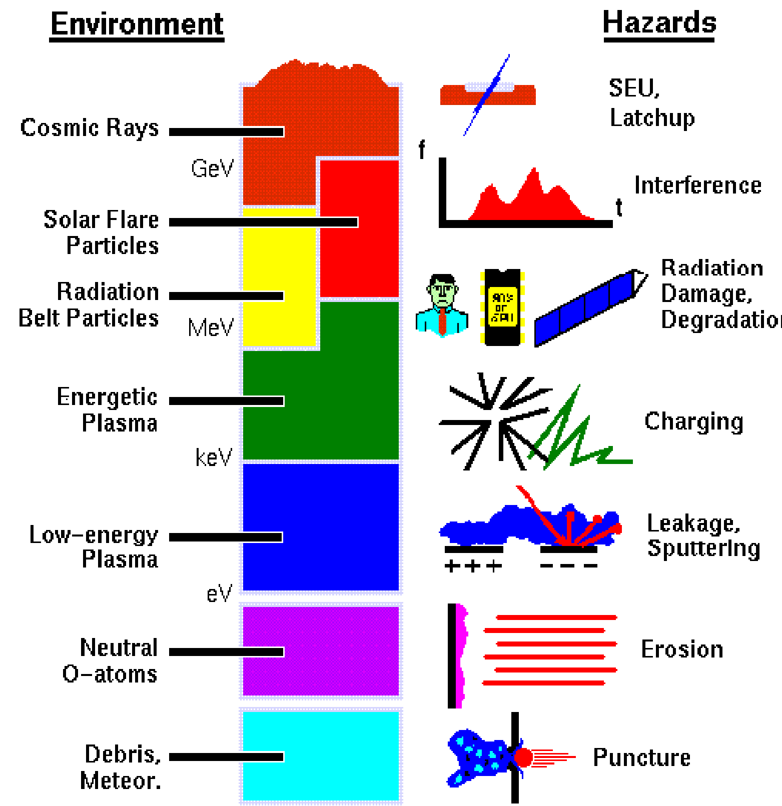
The main sources of energetic particles of concern to spacecraft designers

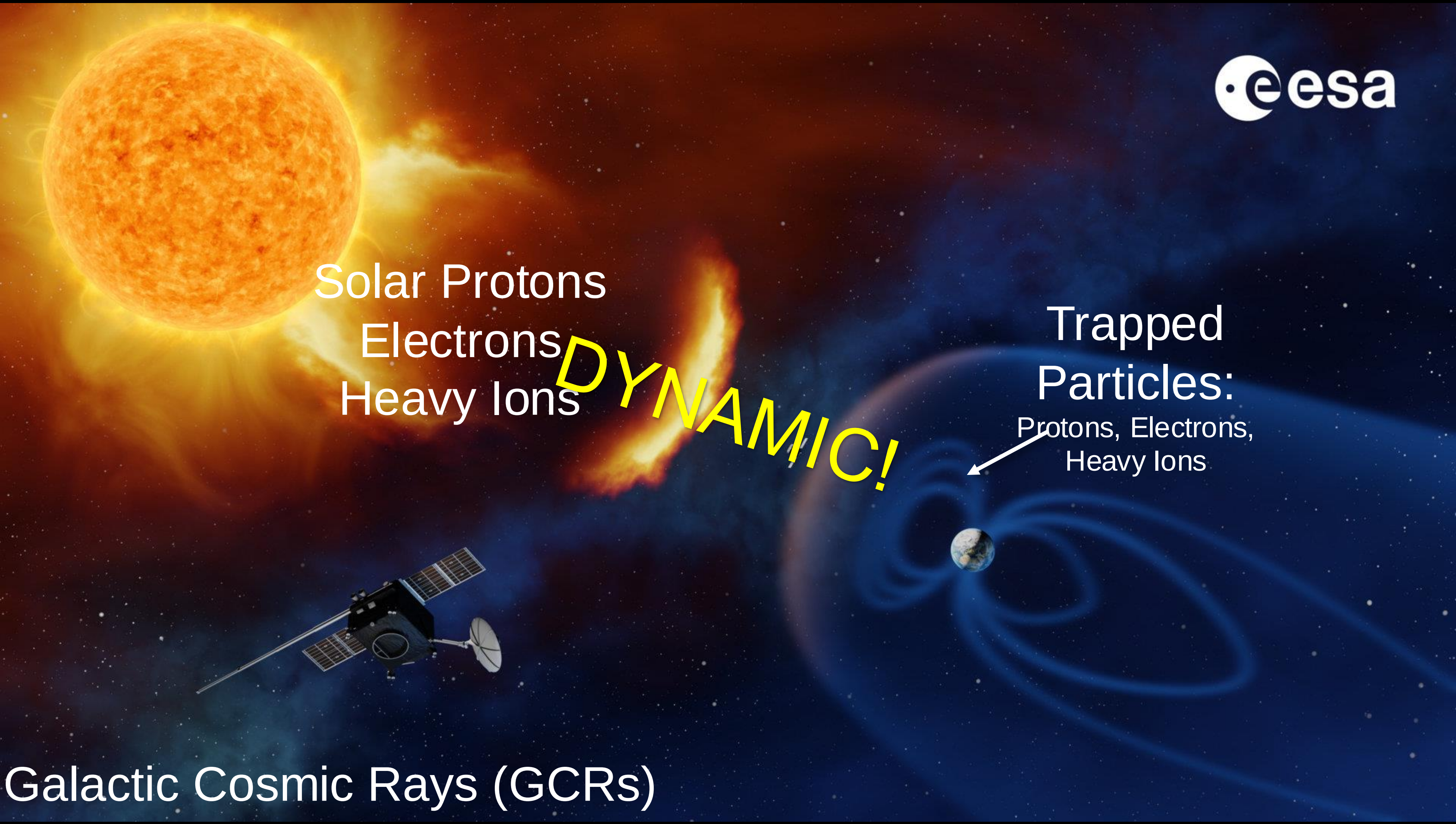
1) cosmic ray protons & heavy ions

2) protons and heavy ions from solar flares

3) protons & electrons trapped in the Van Allen belts

4) heavy ions trapped in the magnetosphere




Solar Protons
Electrons
Heavy Ions
DYNAMIC!
Trapped
Particles:
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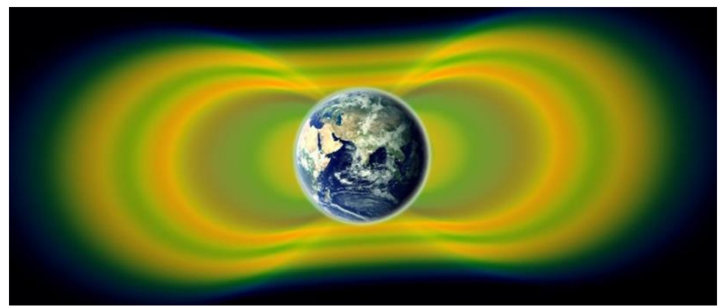
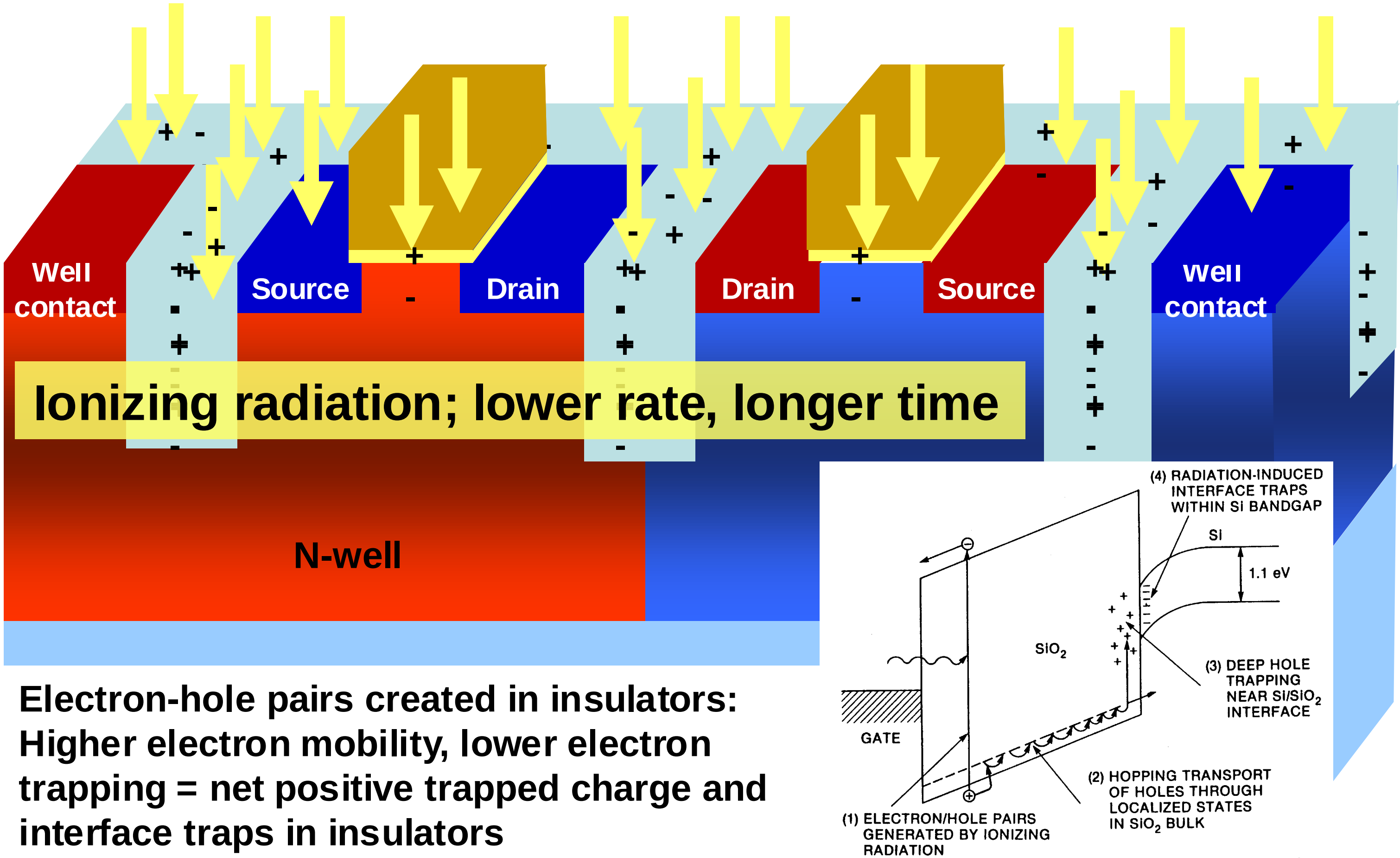
Single-Event Environments

- **Heavy, highly-energetic ions from deep space (galactic cosmic rays)**
- **Energetic protons (trapped in the van Allen radiation belts)**
- **Neutron products (terrestrial pests)**
- **Alpha particles(from contaminants and processing materials)**
- **Muons**



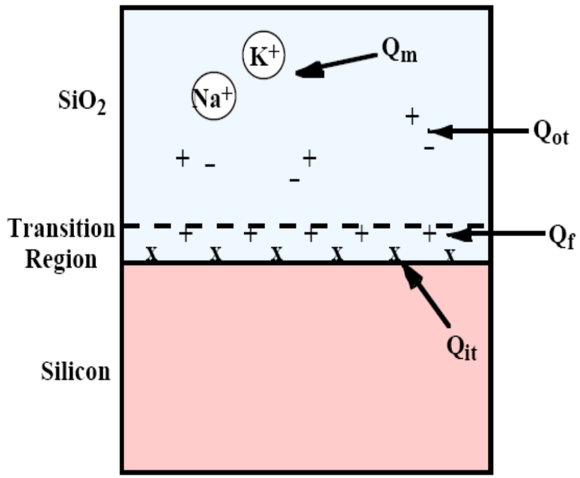
Total Ionizing Dose (TID)



Electron-hole pairs created in insulators: Higher electron mobility, lower electron trapping = net positive trapped charge and interface traps in insulators

McClean, 1987

Electrical Impact of TID



Four charges are associated with insulators and insulator/semiconductor interfaces.

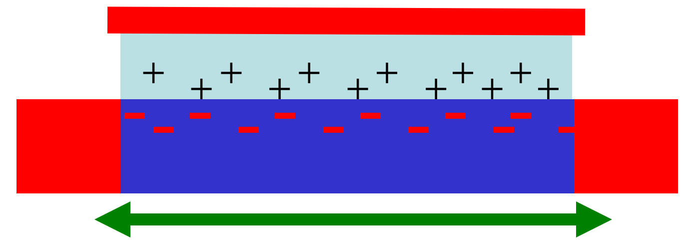
Q_f - fixed oxide charge

Q_{it} - interface trapped charge

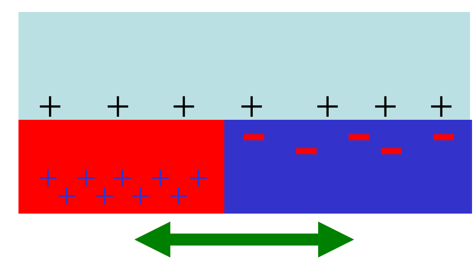
Q_m - mobile oxide charge

Q_{ot} - oxide trapped charge

[20] Plummer, 2000

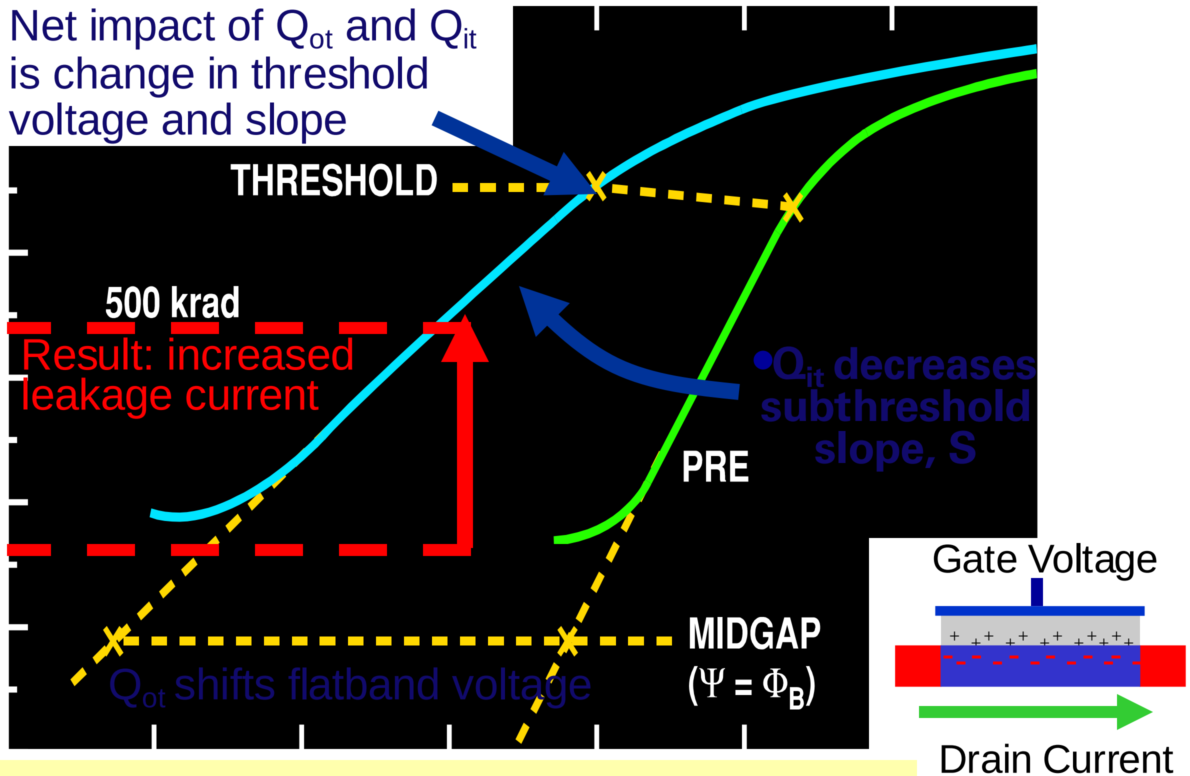


Leakage in N-MOS



Junction Leakage in BJTs

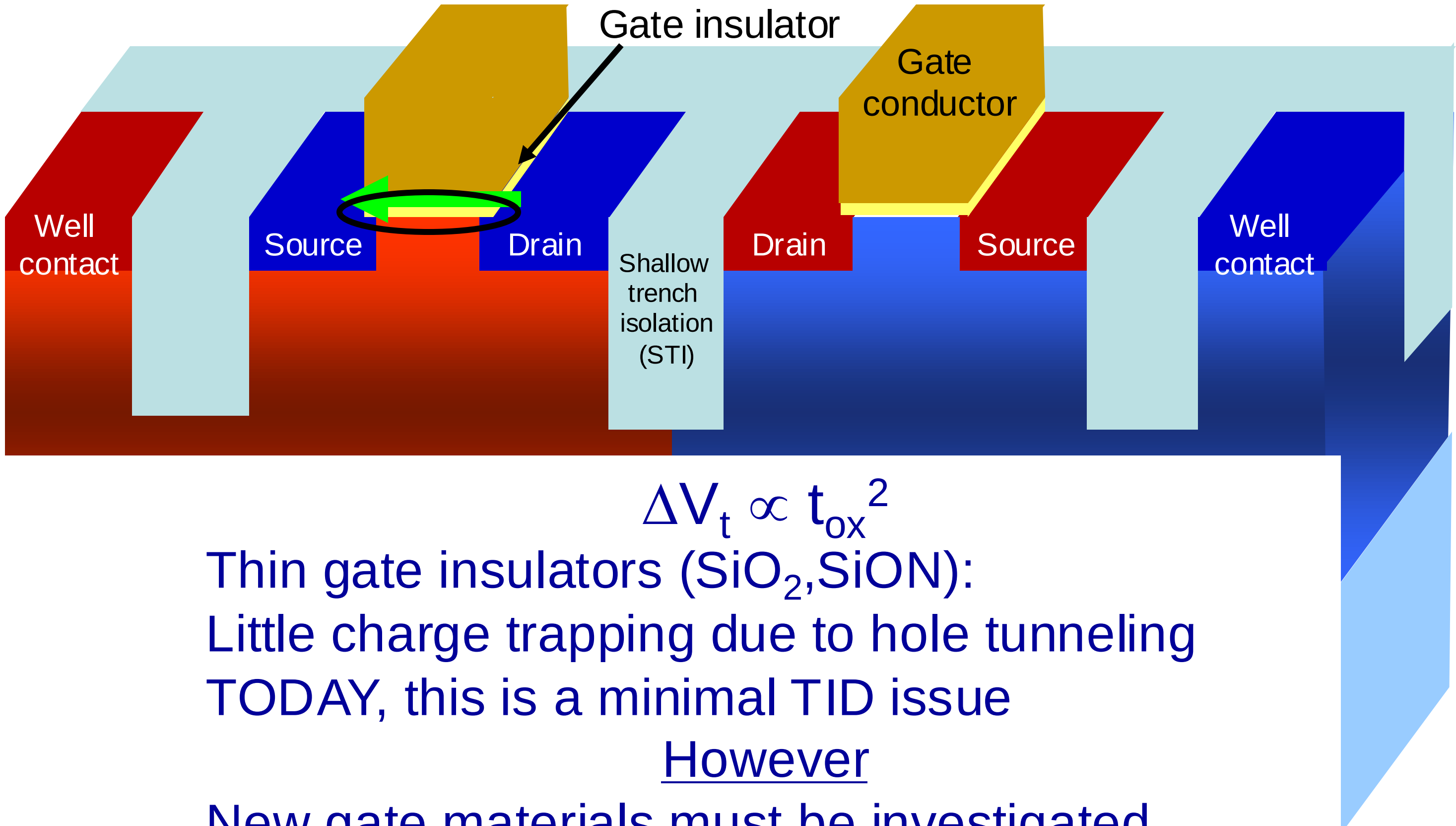
Electrical Impact of TID on MOS



Increased Leakage, Decreased transconductance
(slower, more power consumption)

Schwank, 1994

TID in Gate Insulators



$\Delta V_t \propto t_{ox}^2$

Thin gate insulators (SiO_2,SiON):

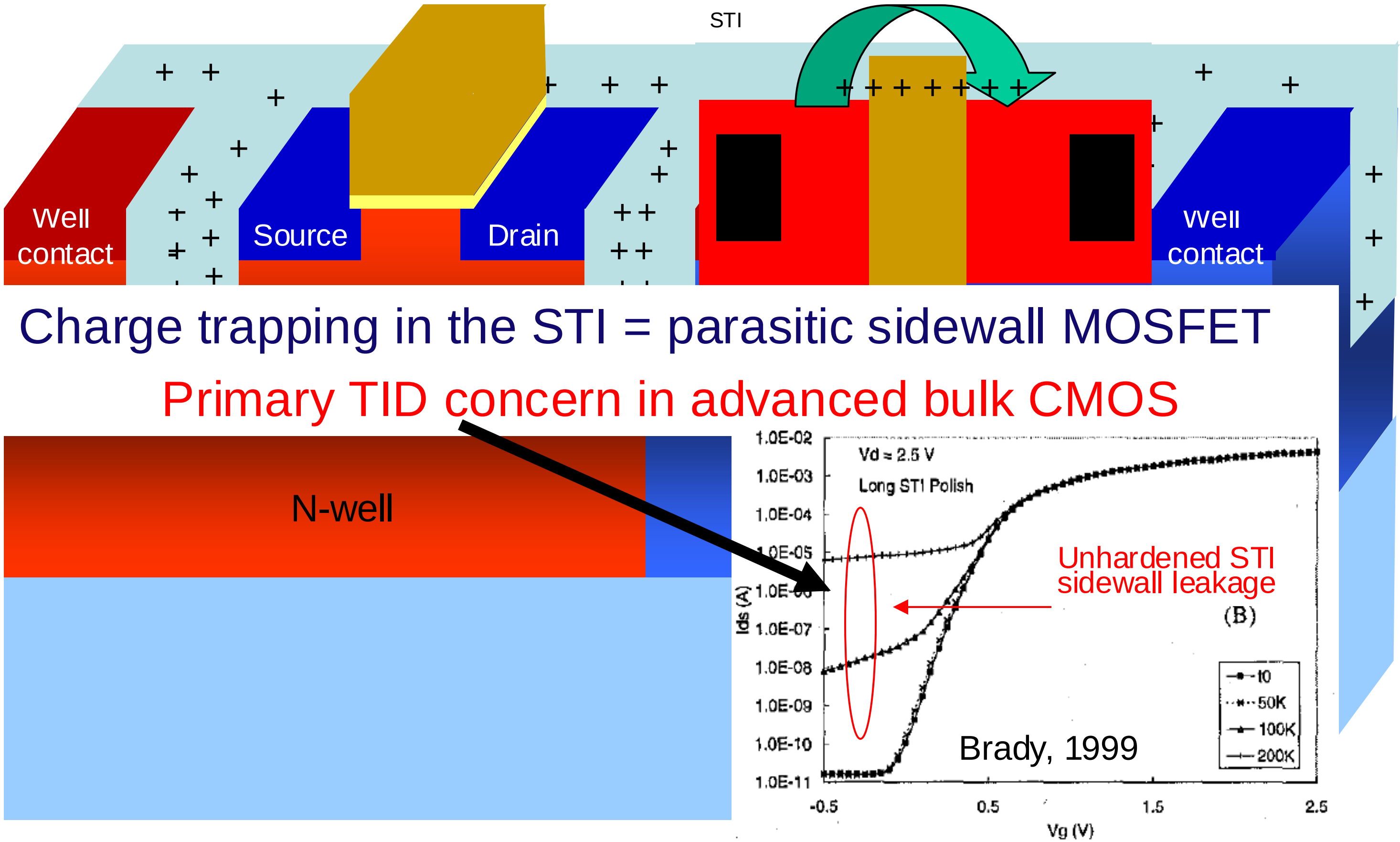
Little charge trapping due to hole tunneling

TODAY, this is a minimal TID issue

<u>However</u>

New gate materials must be investigated

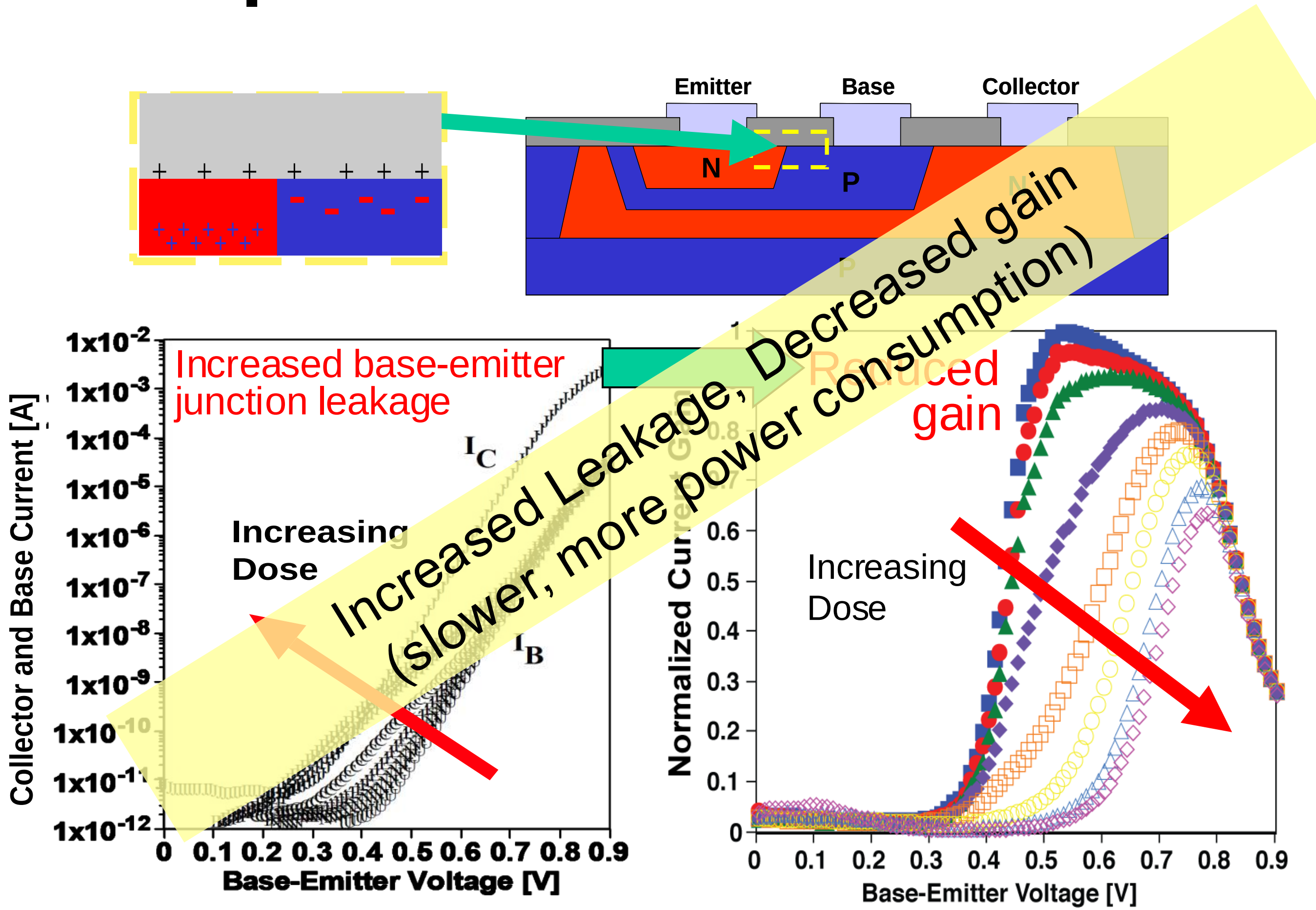
TID in STI Oxides: Intra-Device



Charge trapping in the STI = parasitic sidewall MOSFET

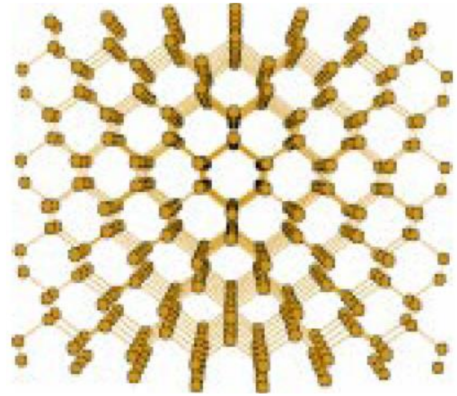
Primary TID concern in advanced bulk CMOS

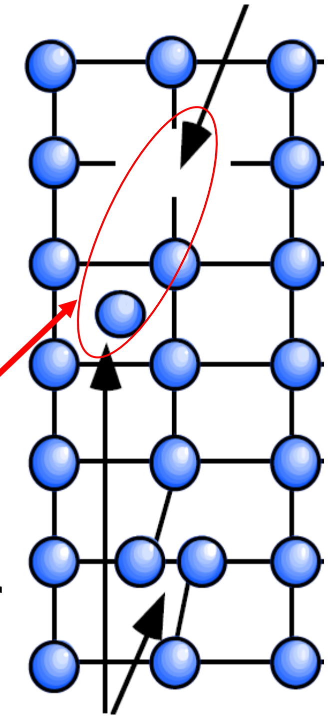
Electrical Impact of TID on BJT



[22] Schrimpf, 2004

Displacement Damage (eps. Neutrons)





Plummer, 2000

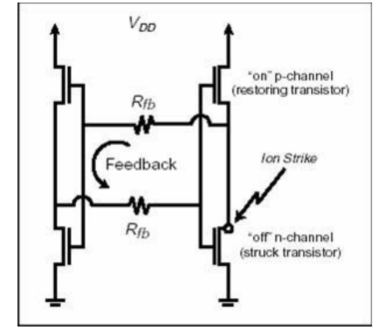
- **Physical displacement of silicon atoms from crystal sites**
- **Results in crystal defects: Frenkel pairs (Interstitial + Vacancy point defects), cluster defects (groups of point defects)**
- **Primarily an issue for bipolar devices, imagers, and solar cells**

Cumulative Dose Environments

- **Space environment or certain ground base sources such as the LHC or nuclear power generation**
- **Ionizing X-rays, Gamma Rays, or high energy particles**
- **Effects due to integrated dose over time**
- **Impact can depend on dose rate**

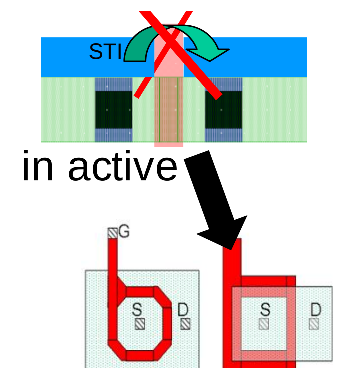
Mitigation

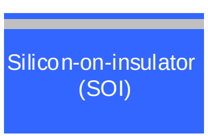
- **System-level management**
  - EDAC, redundancy, voting
  - Circumvention (shut down and restart)
  - Shielding



- **Hardened by design (HBD)**
  - Device layout (ex: annular, edgeless – prohibitive sub 65 nm)
  - Device placement (spacing, interleaving)
  - Guard bands/rings, body contacts, substrate & well contacts
  - Local circuit topology (passive or active temporal filtering, DICE latch, spatial or temporal redundancy)

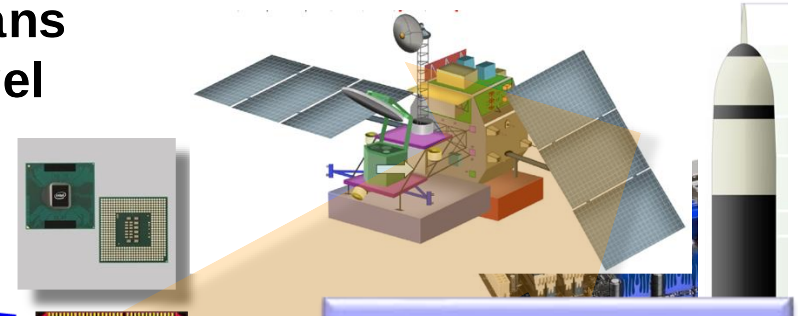
- **Hardened by process (HBP)**
  - Modified materials (balance e-h trapping in minority carrier lifetime reduction material regions)
  - Doping profiles
  - Device structures (FinFETs)
  - Substrate engineering (Ex: epi, doping, SOI)

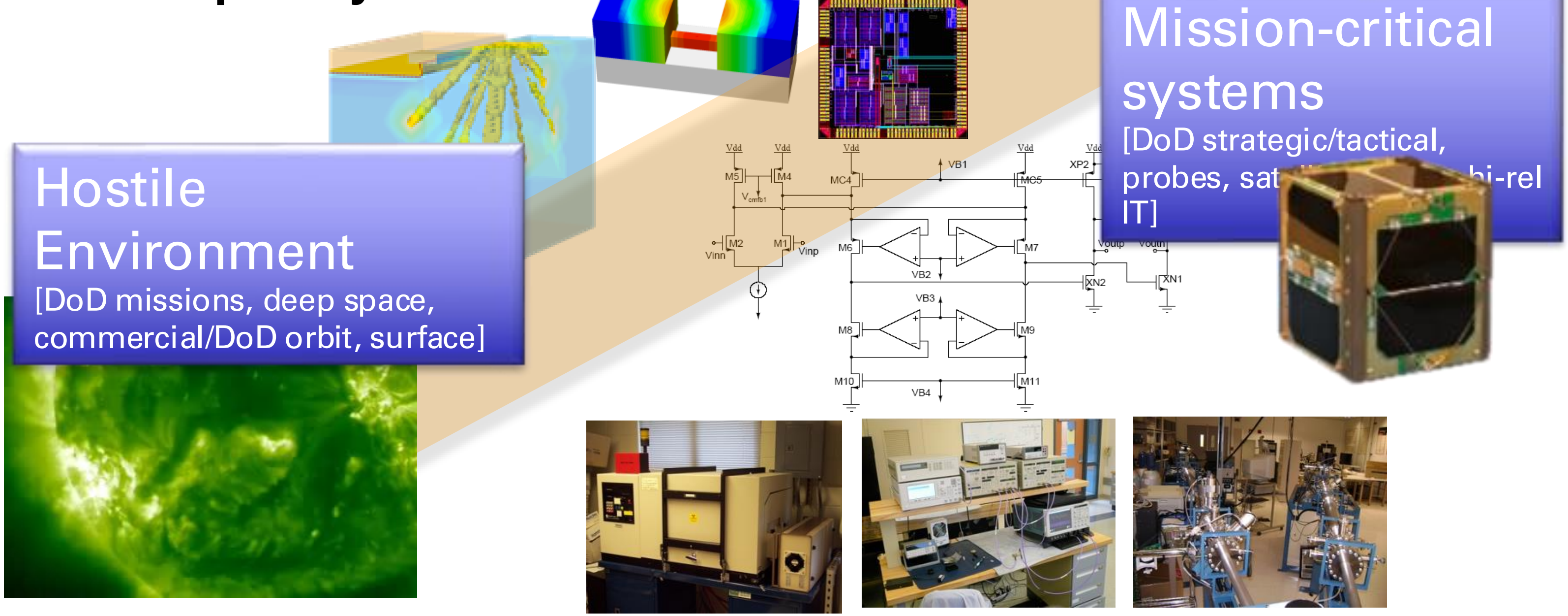




Mechanisms to Missions

- **Radiation effects engineering spans from the atomic to the system level**
- **Testing and modeling/simulation at all levels**
- **Interdisciplinary**





Some useful information

- **SEE**
- **SET**
- **SER**
- **FIT**
- **MBU**
- **SEB**
- **SEGR**
- **LET**
- **TID**
- **NIEL**

1 rad(material) = 100 erg/g energy per unit mass

1 Gy(material) = 1 J/kg [SI unit = Gray, abbrev. Gy]

1 Gy(material) = 100 rad(material) [usually Si or SiO_2]

LET = linear energy transfer = energy per unit mass per unit area transferred from particle to material

Cross-section = area of device that is sensitive to SEE

Material	**Mean E_p (eV)**	**Density (g/cm^3)**	**Pair density, generated per rad, g_0 ($pairs/cm^3$)**
GaAs	**~4.8**	5.32	$\sim 7 \times 10^{13}$
Silicon	**3.6**	2.328	4×10^{13}
Silicon Dioxide	**17**	2.2	8.1×10^{12}